

**/ Descriptions**

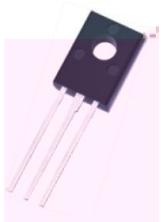
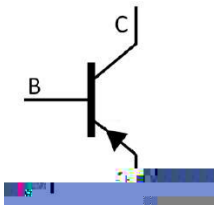
TO-126F          PNP          Silicon PNP transistor in a TO-126F Plastic Package.

**/ Features**

$I_C$      $V_{CE(sat)}$   
High  $I_C$ , low  $V_{CE(sat)}$ .

**/ Applications**

Strobe flash applications, audio power amplifier applications.



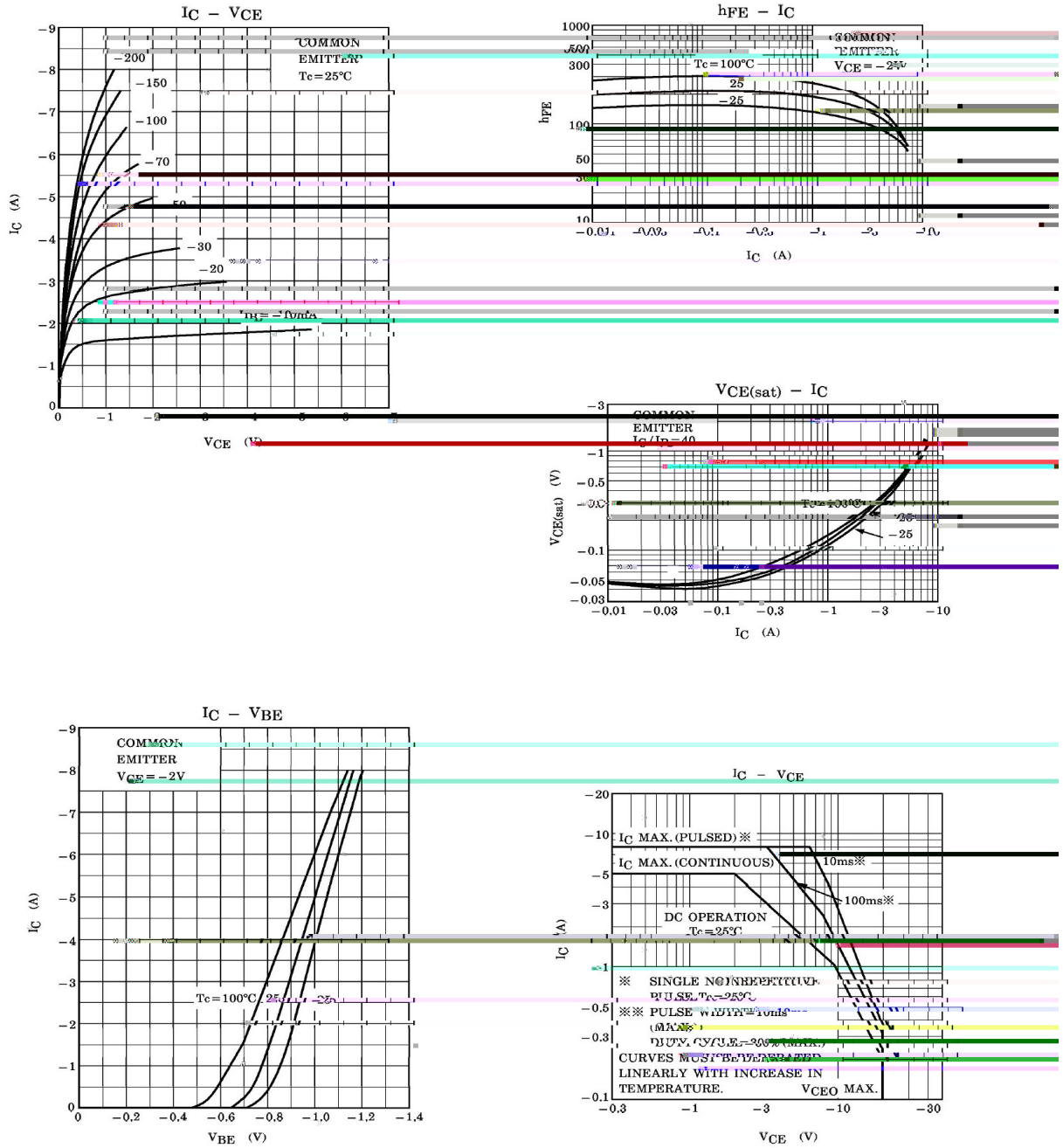
PIN1 Emitter          PIN 2 Collector          PIN 3 Base

**/  $h_{FE}$  Classifications & Marking**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-35	V
Collector to Emitter Voltage	$V_{CEO}$	-20	V
Emitter to Base Voltage	$V_{EBO}$	-8.0	V
Collector Current - Continuous	$I_C$	-5.0	A
Collector Current – Continuous(Pulse)	$I_{CP}$	-8.0	A
Base Current – Continuous	$I_B$	-1.0	A
Collector Power Dissipation	$P_C$	1.5	W
Collector Power Dissipation	$P_C(T_C=25 \text{ }^\circ\text{C})$	10	W
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V					

/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1357

O:  $h_{FE}$

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Note:

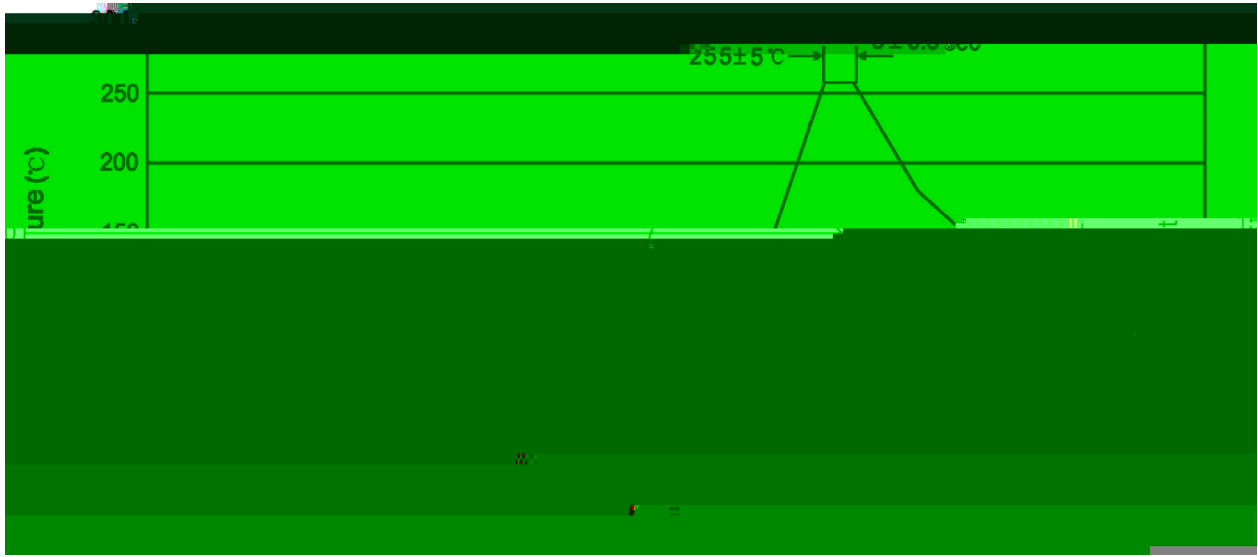
BR: Company Code

A1357: Product Type.

O:  $h_{FE}$  Classifications Symbol

\*\*\*\*: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



- 1            25   150            60   90sec;
- 2            255±5                    5±0.5sec;
- 3                            2   10   /sec.

Note:

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3. Cooling Speed: 2~10 /sec.

255±